

DRV2510-Q1 3-A Automotive Haptic Driver for Solenoids and Voice Coils with Integrated Diagnostics

1 Features

- AEC-Q100 Qualified for automotive applications:
 - Temperature grade 1: -40°C to 125°C , T_A
- Wide operating voltage (4.5 V - 18 V)
- Integrated load-dump protection (40 V)
- High current drive (3 A Peak)
- Low $R_{DS(on)}$, full H-bridge output
- Integrated diagnostics
- Integrated fault protection
 - 40-V Load dump protection per ISO-7637-2
 - Short-circuit protection
 - Over-temperature protection
 - Over-voltage and under-voltage protection
 - Fault reporting
- Analog input
- I²C communication
- Dedicated interrupt pin
- ISO9000: 2002 TS16949 certified

2 Applications

- [Electromagnetic actuator driver](#)
 - Voice coil
 - Solenoid
- [Mechanical button replacement](#)
- [Automotive haptic applications](#)
 - Infotainment
 - Center-console
 - Steering wheel
 - Door-panel
 - Seats

3 Description

The DRV2510-Q1 device is a high current haptic driver specifically designed for inductive loads, such as solenoids and voice coils.

The output stage consists of a full H-bridge capable of delivering 3 A of peak current.

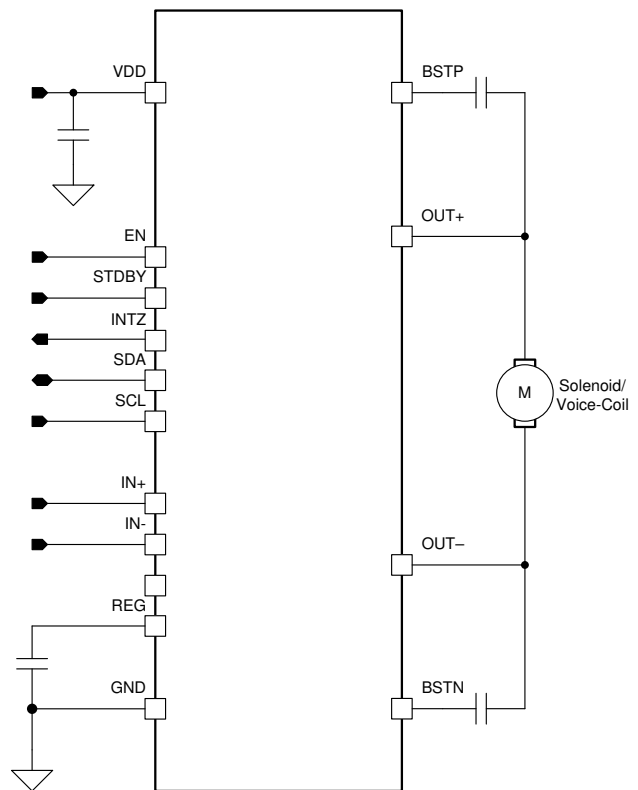
The DRV2510-Q1 device provides protection functions such as undervoltage lockout, over-current protection and over-temperature protection.

The DRV2510-Q1 device is automotive qualified. The integrated load-dump protection reduces external voltage clamp cost and size, and the onboard load diagnostics report the status of the actuator through the digital interface.

Device Information

| PART NUMBER | PACKAGE ⁽¹⁾ | BODY SIZE (NOM) |
|-------------|------------------------|-------------------|
| DRV2510-Q1 | HTSSOP (16) | 5.00 mm x 4.40 mm |

- (1) For all available packages, see the orderable addendum at the end of the data sheet.



Simplified Schematic



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

| Changes from Revision C (May 2020) to Revision D (November 2023) | Page |
|---|-------------|
| • Updated the numbering format for tables, figures, and cross-references throughout the document..... | 1 |

| Changes from Revision B (September 2016) to Revision C (May 2020) | Page |
|--|-------------|
| • Moved automotive <i>Features</i> to the top of the Features list | 1 |
| • Added Junction temperature to the <i>Absolute Maximum Ratings</i> | 5 |
| • Changed the <i>ESD Ratings</i> table..... | 5 |
| • Added INTZ Report to the <i>Electrical Characteristics</i> table..... | 6 |
| • Changed Figure 7-1 | 10 |
| • Changed From: "The load diagnostic function runs on de-assertion" To: "The load diagnostic function runs on assertion" in the <i>Load Diagnostics</i> section..... | 11 |
| • Added the <i>Protection and Monitoring</i> section..... | 12 |
| • Changed From: "NRST pin..." To: "EN pin..." in the <i>Operation in Shutdown Mode</i> section..... | 13 |
| • Changed From: When EN is asserted (logic low) To: When EN is de-asserted (logic low) in the <i>Operation in Shutdown Mode</i> section..... | 13 |
| • Deleted register 0x00 from the <i>Register Map</i> section..... | 17 |
| • Changed register <i>Address: 0x03</i> | 19 |
| • Changed the <i>Single-Ended Source</i> section and Figure 8-1 | 20 |
| • Changed from: BSTA and BSTB to: BSTP and BSTN in the <i>Capacitor Selection</i> section..... | 21 |
| • Changed the <i>Differential Input Diagram</i> section and Figure 8-6 | 23 |

Changes from Revision A (June 2016) to Revision B (September 2016) **Page**

- Changed Feature From: Automotive Qualified (Q100) To: Qualified According to AEC-Q100 Grade 2..... 1
- Changed Feature From: Wide Operating Voltage (5 V – 18 V) To: Wide operating voltage (4.5 V – 18 V)..... 1
- Added Feature: ISO9000: 2002 TS16949 certified 1
- Changed the VDD MIN value From: 5 V to: 4.5 V in the [Section 6.3](#) 5
- Changed From: operates from 5 V – 18 V To: operates from 4.5 V – 18 V in the [Section 9](#) 24

Changes from Revision * (June 2016) to Revision A (June 2016) **Page**

- Released as Production Data. 1
-

5 Pin Configuration and Functions

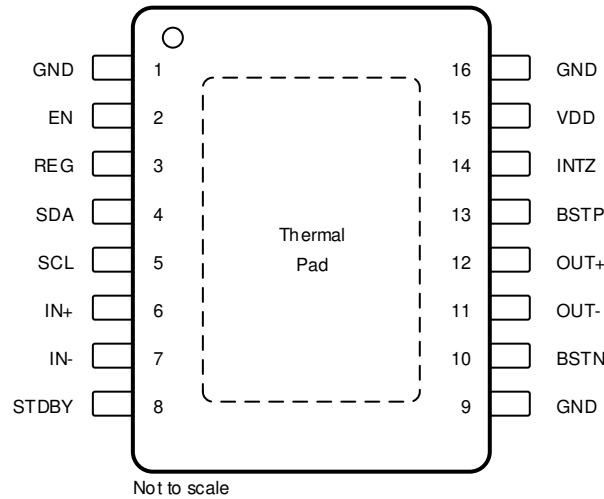


Figure 5-1. TWP Package HTSSOP 16-Pin With Thermal Pad Top View

Table 5-1. Pin Functions

| PIN | | TYPE | DESCRIPTION |
|-------------|----------|------|---|
| NAME | NO. | | |
| GND | 1, 9, 16 | P | Ground. |
| EN | 2 | I | Device enable pin. |
| REG | 3 | P | Internally generated gate voltage supply. Not to be used as a supply or connected to any component other than a 1 μ F X7R ceramic decoupling capacitor and the MODE resistor divider. |
| SDA | 4 | I | I ² C data. |
| SCL | 5 | I | I ² C clock. |
| IN+ | 6 | I | Positive differential input. |
| IN- | 7 | I | Negative differential input. |
| STDBY | 8 | I | Standby pin. |
| BSTN | 10 | P | Boot strap for negative output, connect to 220 nF X5R, or better ceramic cap to OUT-. |
| OUT- | 11 | O | Negative output. |
| OUT+ | 12 | O | Positive output. |
| BSTP | 13 | P | Boot strap for positive output, connect to 220 nF X5R, or better ceramic cap to OUT+. |
| INTZ | 14 | O | General fault reporting. Open drain. INTZ = High, normal operation INTZ = Low, fault condition |
| VDD | 15 | P | Power supply. |
| Thermal Pad | | G | Connect to GND for best system performance. If not connected to GND, leave floating. |

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

| | | MIN | MAX | UNIT |
|--|--|------|-----|------|
| Supply voltage | VDD DC supply voltage range | -0.3 | 30 | V |
| | VDD pulsed supply voltage range. t < 400 ms exposure | -1 | 40 | |
| | VDD supply voltage ramp rate | | 15 | V/ms |
| Input voltage, V _I | SCL, SDA, EN | -0.3 | 5 | V |
| | IN+, IN-, STDBY | -0.3 | 6.5 | |
| Current | DC current on VDD, GND, OUT+, OUT- | -4 | 4 | A |
| | Maximum current in all input pins | -1 | 1 | mA |
| | Maximum sink current for open-drain pins | | 7 | |
| Operating free-air temperature, T _A | | -40 | 125 | °C |
| Junction temperature, T _J | | -40 | 150 | |
| Storage temperature range, T _{stg} | | -55 | 150 | |

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

| | | VALUE | UNIT |
|--|--|-------|------|
| V _(ESD) Electrostatic discharge | Human body model (HBM), per AEC Q100-002 ⁽¹⁾ HBM ESD Classification Level H2 | ±3500 | V |
| | Charged device model (CDM), per AEC Q100-011 CDM ESD Classification Level C4B | ±1000 | |

- (1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

| | | MIN | NOM | MAX | UNIT |
|-----------------|--|-----|-----|-----|------|
| VDD | Supply voltage. VDD. | 4.5 | | 18 | V |
| V _{IH} | High-level input voltage. SDA, SCL, STDBY, EN. | 2.1 | | | V |
| V _{IL} | Low-level input voltage. SDA, SCL, STDBY, EN | | | 0.7 | V |
| V _{OL} | Low-level output voltage | | | 0.4 | V |
| V _{OH} | High-level output voltage | 2.4 | | | V |
| I _{IH} | High-level input current. SDA, SCL, STDBY, EN | | | 50 | µA |
| R _L | Minimum load impedance | | 1.5 | | Ω |
| C _B | Load capacitance for each bus line (SDA/SCL) | | | 400 | pF |

6.4 Thermal Information

| THERMAL METRIC ⁽¹⁾ | | DRV2510-Q1 | UNIT |
|-------------------------------|--|--------------|------|
| | | PWP (HTSSOP) | |
| | | {16} PINS | |
| R _{θJA} | Junction-to-ambient thermal resistance | 39.4 | °C/W |
| R _{θJC(top)} | Junction-to-case (top) thermal resistance | 24.9 | °C/W |
| R _{θJB} | Junction-to-board thermal resistance | 20 | °C/W |
| ψ _{JT} | Junction-to-top characterization parameter | 0.6 | °C/W |
| ψ _{JB} | Junction-to-board characterization parameter | 19.8 | °C/W |

| THERMAL METRIC ⁽¹⁾ | | DRV2510-Q1 | UNIT |
|-------------------------------|--|--------------|------|
| | | PWP (HTSSOP) | |
| | | {16} PINS | |
| R _{θJC(bot)} | Junction-to-case (bottom) thermal resistance | 2 | °C/W |

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics

T_A = 25°C, AVCC = VDD = 12 V, R_L = 5 Ω (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--------------------------|--|--|-----|------|-----|------|
| V _{OS} | Output offset voltage (measured differentially) | V _I = 0 V, Gain = 20 dB | -25 | | 25 | mV |
| I _{VDD} | Quiescent supply current | No load or filter | | 16 | | mA |
| I _{VDD(SD)} | Quiescent supply current in shutdown mode | No load or filter | | 5 | 20 | μA |
| I _{VDD(STD BY)} | Quiescent supply current in standby mode | No load or filter | | 7 | | mA |
| r _{DS(on)} | Drain-source on-state resistance, measured pin to pin | T _J = 25°C | | 180 | | mΩ |
| G | Gain | P _(o) = 1 W | 19 | 20 | 21 | dB |
| | | | 25 | 26 | 27 | |
| | | | 31 | 32 | 33 | dB |
| | | | 35 | 36 | 37 | |
| V _{REG} | Regulator voltage | | 6.4 | 6.9 | 7.4 | V |
| V _O | Output voltage (measured differentially) | | | 20 | | V |
| PSRR | Power supply ripple rejection | VDD = 12 V + 1 Vrms at 1 kHz | | 75 | | dB |
| V _{ICMIN} | Input common-mode min | | | 0.3 | | V |
| V _{ICMAX} | Input common-mode max | | | 4.4 | | |
| CMRR | Common-mode rejection ratio | f = 1 kHz, 100 mVrms referenced to GND. Gain = 20 dB | | 63 | | dB |
| f _{OSC} | Oscillator frequency (with PWM duty cycle < 96%) | | | 400 | | kHz |
| | | | | 500 | | |
| | Output resistance in shutdown | | | 10 | | MΩ |
| | Resistance to detect a short from OUT pin(s) to VDD or GND | | | | 200 | Ω |
| | Open-circuit detection threshold | | 75 | 95 | 120 | Ω |
| | Short-circuit detection threshold | | 0.9 | 1.2 | 1.5 | Ω |
| | Power-on threshold | | | 4.1 | | V |
| | Thermal trip point | | | 150 | | °C |
| | Thermal hysteresis | | | 15 | | °C |
| | Over-current trip point | | | 3.5 | | A |
| | Over-voltage trip point | | | 21 | | V |
| | Over-voltage hysteresis | | | 0.6 | | V |
| | Under-voltage trip point | | | 4 | | V |
| | Under-voltage hysteresis | | | 0.25 | | V |
| INTZ Report | | | | | | |
| | INTZ pin output voltage for logic-level high (open-drain logic output) | External 47-kΩ pullup resistor to 3.3 V | 2.4 | | | V |
| | INTZ pin output voltage for logic-level low (open-drain logic output) | External 47-kΩ pullup resistor to 3.3 V | | | 0.5 | V |

6.6 Timing Requirements

T_A = 25 °C, V_{DD} = 3.6 V (unless otherwise noted)

| | | MIN | NOM | MAX | UNIT |
|--------------------|--|-----|-----|-----|------|
| f _(SCL) | Frequency at the SCL pin with no wait states | | | 400 | kHz |
| t _{w(H)} | Pulse duration, SCL high | 0.6 | | | µs |
| t _{w(L)} | Pulse duration, SCL low | 1.3 | | | µs |
| t _{su(1)} | Setup time, SDA to SCL | 100 | | | ns |
| t _{h(1)} | Hold time, SCL to SDA | 300 | | | ns |
| t _(BUF) | Bus free time between stop and start condition | 1.3 | | | µs |
| t _{su(2)} | Setup time, SCL to start condition | 0.6 | | | µs |
| t _{h(2)} | Hold time, start condition to SCL | 0.6 | | | µs |
| t _{su(3)} | Setup time, SCL to stop condition | 0.6 | | | µs |

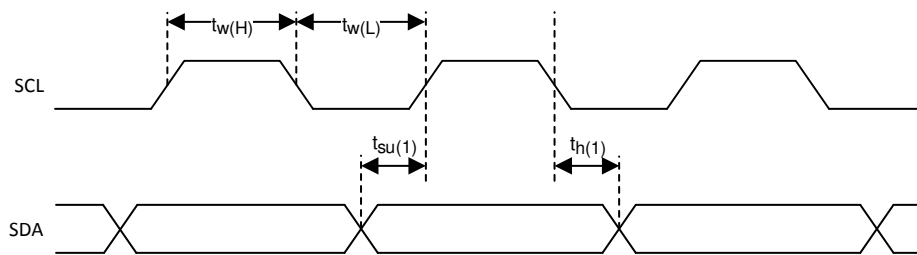


Figure 6-1. SCL and SDA Timing

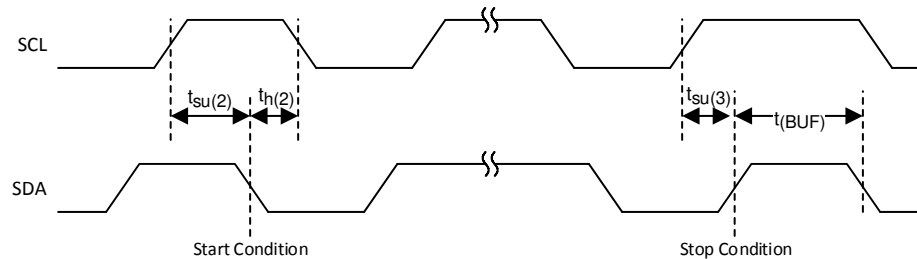


Figure 6-2. Timing for Start and Stop Conditions

6.7 Switching Characteristics

over operating free-air temperature range (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|-----------------------|--|-----|-----|-----|------|
| t _{on-sd} | Turn-on time from shutdown to waveform EN = Low to High, STBY = Low | | 229 | | ms |
| t _{OFF-sd} | Turn-off time EN = High to Low | | 47 | | µs |
| t _{on-stbby} | Turn-on time from standby to waveform EN = High, STBY = High to Low | | 32 | | µs |

6.8 Typical Characteristics

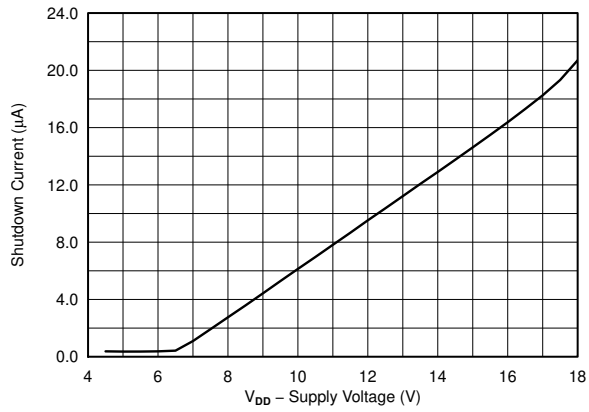


Figure 6-3. Shutdown Current vs VDD Voltage

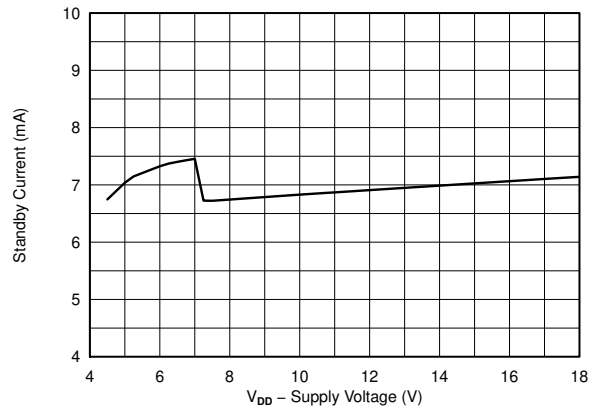


Figure 6-4. Standby Current vs VDD Voltage

7 Detailed Description

7.1 Overview

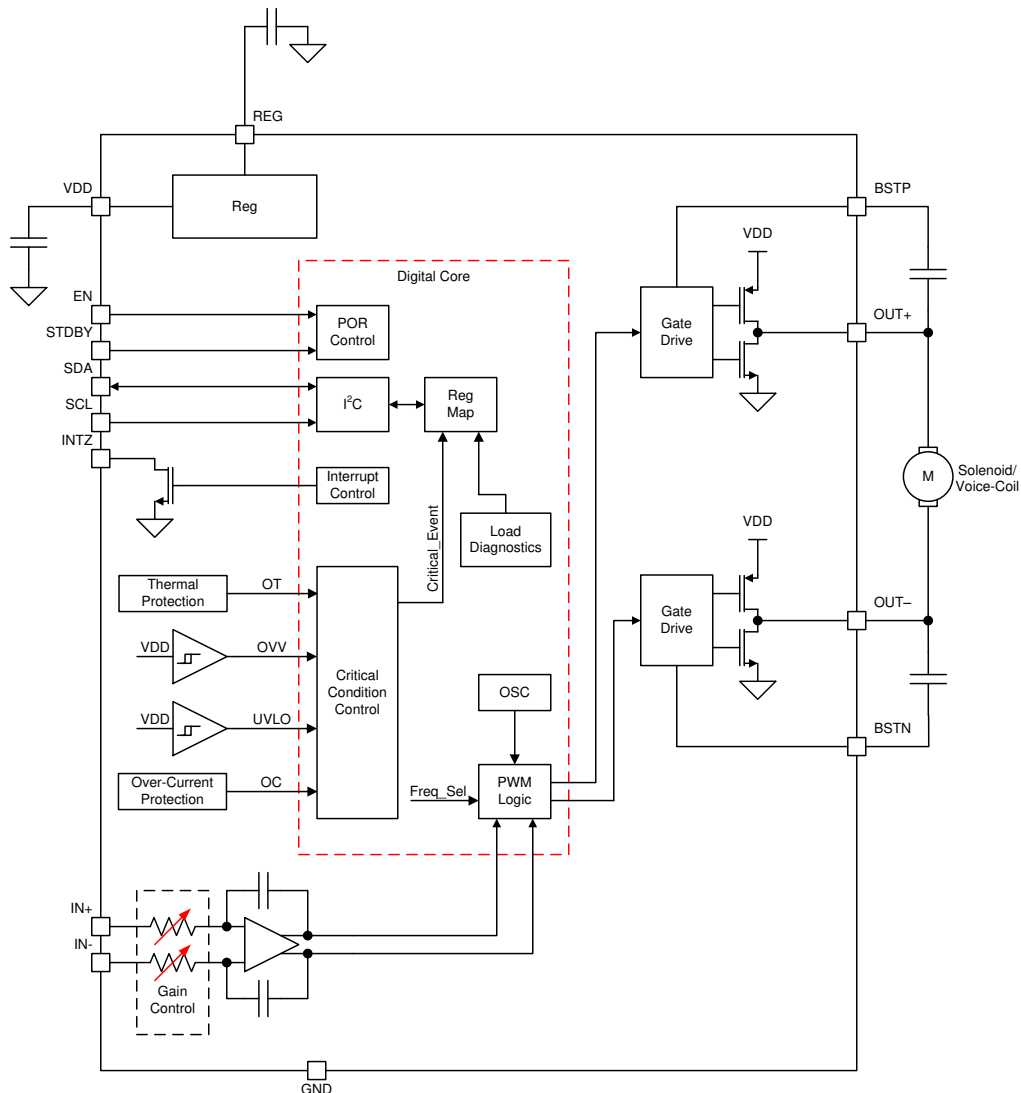
The DRV2510-Q1 device is a high current haptic driver specifically designed for inductive loads, such as solenoids and voice coils.

The output stage consists of a full H-bridge capable of delivering 3 A of peak current.

The design uses an ultra-efficient switching output technology developed by Texas Instruments, but with features added for the automotive industry. The DRV2510-Q1 device provides protection functions such as undervoltage lockout, over-current protection and over-temperature protection. This technology allows for reduced power consumption, reduced heat, and reduced peak currents in the electrical system.

The DRV2510-Q1 device is automotive qualified. The integrated load-dump protection reduces external voltage clamp cost and size, and the onboard load diagnostics report the status of the actuator through the digital interface.

7.2 Functional Block Diagram



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7.3 Feature Description

7.3.1 Analog Input and Configurable Pre-amplifier

The DRV2510-Q1 device features a differential input stage that cancels common-mode noise that appears on the inputs. The DRV2510-Q1 device also features four gain settings that are configurable via I²C. Please see the Programming Sections for register locations.

Table 7-1. Gain Configuration Table

| GAIN | INPUT IMPEDANCE |
|-------|-----------------|
| 20 dB | 60 kΩ |
| 26 dB | 30 kΩ |
| 32 dB | 15 kΩ |
| 36 dB | 9 kΩ |

7.3.2 Pulse-Width Modulator (PWM)

The DRV2510-Q1 device features BD modulation scheme with high bandwidth, low noise, low distortion, and excellent stability.

The BD modulation scheme allows for smaller ripple currents through the load. Each output switches from 0 V to the supply voltage. With no input, the OUT+ and OUT- pins are in phase with each other so that there is little or no current in the load. For positive differential inputs, the duty cycle of OUT+ is greater than 50% and the duty cycle of OUT- is lower than 50% for a positive differential output voltage. The opposite is true for negative differential inputs. The voltage across the load sits at 0 V throughout most of the switching period, reducing the switching current, which reduces the I²R losses in the load.

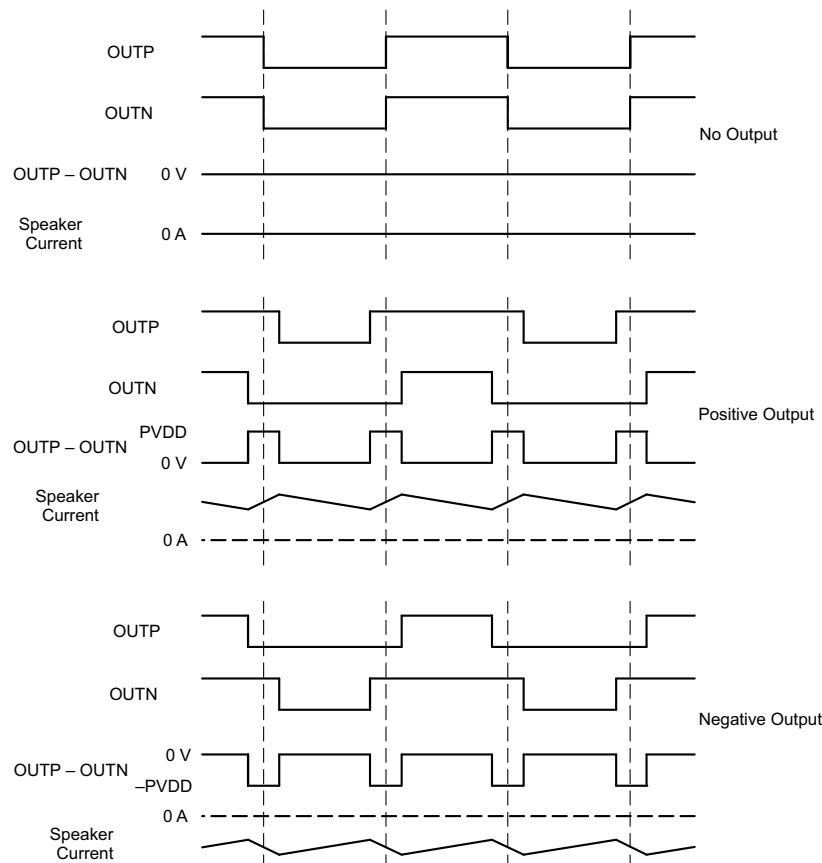


Figure 7-1. BD Mode Modulation

7.3.3 Designed for low EMI

The DRV2510-Q1 device design has minimal parasitic inductances due to the short leads on the package. This dramatically reduces EMI that results from current passing from the die to the system PCB. The design incorporates circuitry that optimizes output transitions that causes EMI. Follow the recommended design requirements in the [Section 8.2.1.1](#) section.

7.3.4 Device Protection Systems

The DRV2510-Q1 device features a complete set of protection circuits carefully designed to protect the device against permanent failures due to shorts, over-temperature, over-voltage, and under-voltage scenarios. The INTZ pin signals if an error is detected.

Additionally, the DRV2510-Q1 device is not damaged by adjacent pin to pin shorts.

Table 7-2. Fault Reporting Table

| FAULT | TRIGGERING CONDITION | INTZ | ACTION |
|------------------|-------------------------------------|------------|---|
| Over-current | Output short or short to VDD or GND | pulled low | output in high impedance. I ² updated. |
| Over-temperature | T _j > 150 °C | pulled low | output in high impedance. Recovery is automatic once the temperature returns to a safe level. |
| Under-voltage | VDD < 4 V | pulled low | output in high impedance. I ² reset. |
| Over-voltage | VDD > 21 V | pulled low | output in high impedance. I ² updated. |

7.3.4.1 Diagnostics

The device incorporates load diagnostic circuitry designed for detecting and determining the status of output connections. The device supports the following diagnostics:

- Short to GND
- Short to VDD
- Short across load
- Open load

The device reports the presence of any of the short or open conditions to the system via I²C register read.

7.3.4.1.1 Load Diagnostics

The load diagnostic function runs on assertion of EN or when the device is in a fault state (dc detect, overcurrent, overvoltage, undervoltage, and overtemperature). During this test, the outputs are in a Hi-Z state. The device determines whether the output is a short to GND, short to VDD, open load, or shorted load. The load diagnostic biases the output, which therefore requires limiting the capacitance value for proper functioning. The load diagnostic test takes approximately 229 ms to run. Note that the *check* phase repeats up to five times if a fault is present or a large capacitor to GND is present on the output. On detection of an open load, the output still operates. On detection of any other fault condition, the output goes into a Hi-Z state, and the device checks the load continuously until removal of the fault condition. After detection of a normal output condition, the output starts. The load diagnostics run after every other overvoltage (OV) event. The load diagnostic for open load only has I²C reporting. All other faults have I²C and INTZ pin assertion.

The device performs load diagnostic tests as shown in [Figure 7-2](#).

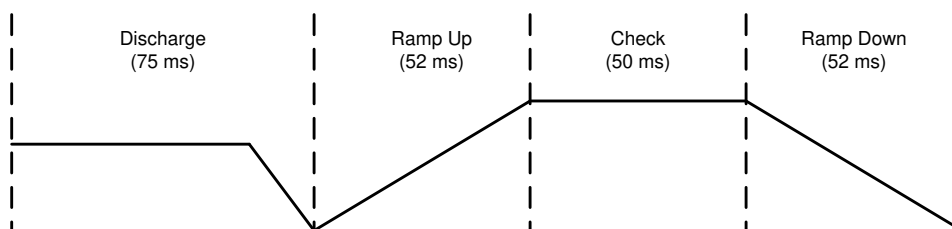


Figure 7-2. Load Diagnostics Sequence of Events

Figure 7-3 illustrates how the diagnostics determine the load based on output conditions.

| | Output Conditions | Load Diagnostics |
|--------|---------------------------------------|--|
| OL Max | Open Load | Open Load Detected |
| OL Min | Open Load (OL) Detection Threshold | Normal or Open Load May Be Detected |
| SL Max | Normal Load | Play Mode |
| SL Min | Shorted Load (SL) Detection Threshold | Normal or Shorted Load May Be Detected |
| | Shorted Load | Shorted Load Detected |

Figure 7-3. Load Diagnostic Reporting Thresholds

7.3.4.2 Faults During Load Diagnostics

If the device detects a fault (overtemperature, overvoltage, undervoltage) during the load diagnostics test, the device exits the load diagnostics, which may result in a small transient on the output.

7.3.4.3 Protection and Monitoring

- **Overcurrent Shutdown (OCSD)**—The overcurrent shutdown forces the output into Hi-Z. The device asserts the INTZ pin and updates the I²C register.
- **DC Detect**—This circuit checks for a dc offset continuously during normal operation at the output of the amplifier. If a dc offset occurs, the device asserts the INTZ pin and updates the I²C register. Note that the dc detection threshold follows VDD changes.
- **Overtemperature Shutdown (OTSD)**—The device shuts down when the die junction temperature reaches the overtemperature threshold. The device asserts the INTZ pin and updates I²C register. Recovery is automatic when the temperature returns to a safe level.
- **Undervoltage (UV)**—The undervoltage (UV) protection detects low voltages on VDD. In the event of an undervoltage condition, the device asserts the INTZ pin and resets the I²C register.
- **Power-On Reset (POR)**—Power-on reset (POR) occurs when VDD drops below the POR threshold. A POR event causes the I²C bus to go into a high-impedance state. After recovery from the POR event, the device restarts automatically with default I²C register settings. The I²C is active as long as the device is not in POR.
- **Overvoltage (OV) and Load Dump**—OV protection detects high voltages on VDD. If VDD reaches the overvoltage threshold, the device asserts the INTZ pin and updates the I²C register. The device can withstand 40-V load-dump voltage spikes.
- **SpeakerGuard™**—This protection circuitry limits the output voltage to the value selected in I²C register 0x03. This value determines both the positive and negative limits. The user can use the SpeakerGuard feature to improve battery life or protect the actuator from exceeding its excursion limits.
- **Adjacent-Pin Shorts**—The device design is such that shorts between adjacent pins do not cause damage.

7.4 Device Functional Modes

The DRV2510-Q1 device has multiple power states to optimize power consumption.

7.4.1 Operation in Shutdown Mode

The EN pin of the DRV2510-Q1 device puts the device in a shutdown mode. When EN is de-asserted (logic low), all internal blocks of the device are off to achieve ultra low power. I²C is not operational in this mode and the output is in Hi-Z state.

7.4.2 Operation in Standby Mode

The STDBY pin of the DRV2510-Q1 device puts the device in a standby mode. When STDBY is asserted (logic high), some internal blocks of the device are off to achieve low power while preserving the ability to wake up quickly to achieve low latency waveform playback.

7.4.3 Operation in Active Mode

The DRV2510-Q1 device is in active mode when it has a valid supply, and it is not in either shutdown or standby modes. In this mode the DRV2510-Q1 device is fully on and reproducing at the output the input times the gain.

7.5 Programming

7.5.1 General I²C Operation

The I²C bus employs two signals, SDA (data) and SCL (clock), to communicate between integrated circuits in a system. The bus transfers data serially, one bit at a time. The 8-bit address and data bytes are transferred with the most-significant bit (MSB) first. In addition, each byte transferred on the bus is acknowledged by the receiving device with an acknowledge bit. Each transfer operation begins with the master device driving a start condition on the bus and ends with the master device driving a stop condition on the bus. The bus uses transitions on the data pin (SDA) while the clock is at logic high to indicate start and stop conditions. A high-to-low transition on the SDA signal indicates a start, and a low-to-high transition indicates a stop. Normal data-bit transitions must occur within the low time of the clock period. Figure 7-4 shows a typical sequence. The master device generates the 7-bit slave address and the read-write (R/W) bit to start communication with a slave device. The master device then waits for an acknowledge condition. The slave device holds the SDA signal low during the acknowledge clock period to indicate acknowledgment. When the acknowledgment occurs, the master transmits the next byte of the sequence. Each device is addressed by a unique 7-bit slave address plus a R/W bit (1 byte). All compatible devices share the same signals through a bidirectional bus using a wired-AND connection.

The number of bytes that can be transmitted between start and stop conditions is not limited. When the last word transfers, the master generates a stop condition to release the bus. Figure 7-4 shows a generic data-transfer sequence.

Use external pull-up resistors for the SDA and SCL signals to set the logic-high level for the bus. Pull-up resistors between 660 Ω and 4.7 k Ω are recommended. Do not allow the SDA and SCL voltages to exceed the DRV2510-Q1 supply voltage, V_{DD} .

Note

The DRV2510-Q1 slave address is 0x6C (7-bit), or 1101100 in binary.

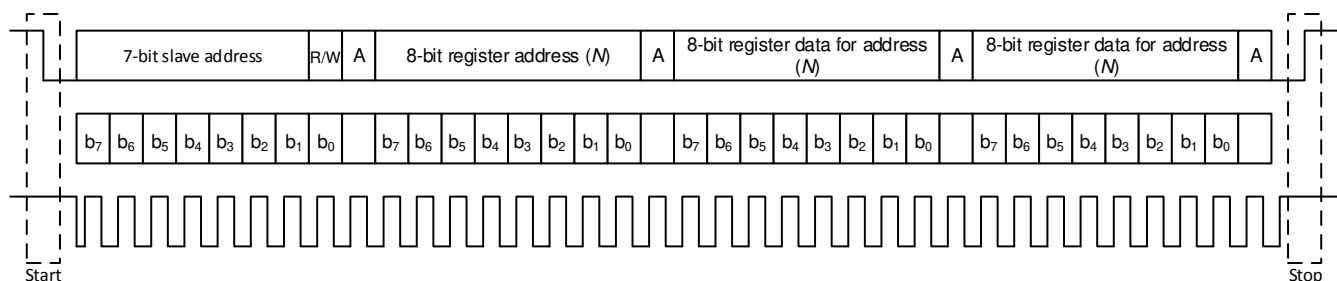


Figure 7-4. Typical I²C Sequence

The DRV2510-Q1 device operates as an I²C-slave 1.8-V logic thresholds, but can operate up to the V_{DD} voltage. The device address is 0x5A (7-bit), or 1011010 in binary which is equivalent to 0xB4 (8-bit) for writing and 0xB5 (8-bit) for reading.

7.5.2 Single-Byte and Multiple-Byte Transfers

The serial control interface supports both single-byte and multiple-byte R/W operations for all registers.

During multiple-byte read operations, the DRV2510-Q1 device responds with data one byte at a time and begins at the signed register. The device responds as long as the master device continues to respond with acknowledges.

The DRV2510-Q1 supports sequential I²C addressing. For write transactions, a sequential I²C write transaction has taken place if a register is issued followed by data for that register as well as the remaining registers that follow. For I²C sequential-write transactions, the register issued then serves as the starting point and the amount of data transmitted subsequently before a stop or start is transmitted determines how many registers are written.

7.5.3 Single-Byte Write

As shown in Figure 7-5, a single-byte data-write transfer begins with the master device transmitting a start condition followed by the I²C device address and the read-write bit. The read-write bit determines the direction of the data transfer. For a write-data transfer, the read-write bit must be set to 0. After receiving the correct I²C device address and the read-write bit, the DRV2510-Q1 responds with an acknowledge bit. Next, the master transmits the register byte corresponding to the DRV2510-Q1 internal-memory address that is accessed. After receiving the register byte, the device responds again with an acknowledge bit. Finally, the master device transmits a stop condition to complete the single-byte data-write transfer.

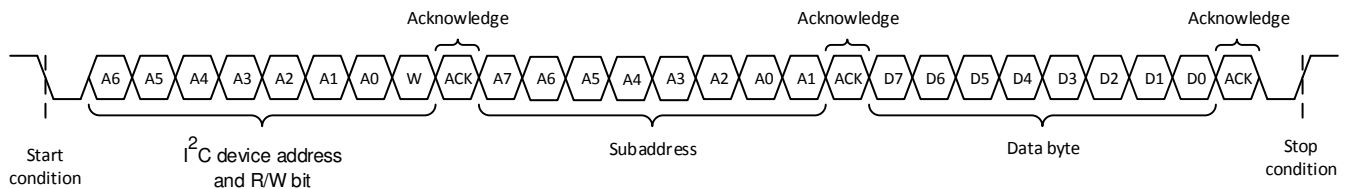


Figure 7-5. Single-Byte Write Transfer

7.5.4 Multiple-Byte Write and Incremental Multiple-Byte Write

A multiple-byte data write transfer is identical to a single-byte data write transfer except that multiple data bytes are transmitted by the master device to the DRV2510-Q1 device as shown in Figure 7-6. After receiving each data byte, the DRV2510-Q1 device responds with an acknowledge bit.

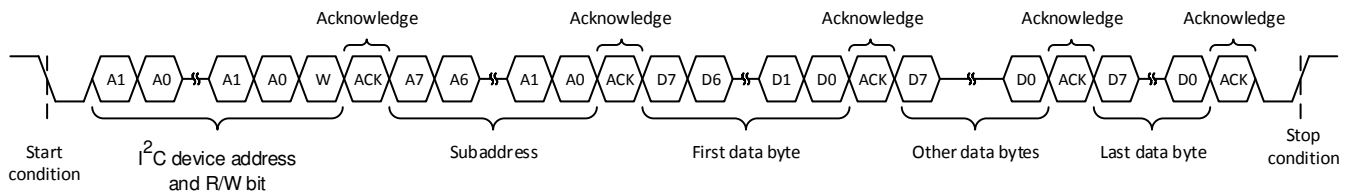


Figure 7-6. Multiple-Byte Write Transfer

7.5.5 Single-Byte Read

Figure 7-7 shows that a single-byte data-read transfer begins with the master device transmitting a start condition followed by the I²C device address and the read-write bit. For the data-read transfer, both a write followed by a read actually occur. Initially, a write occurs to transfer the address byte of the internal memory address to be read. As a result, the read-write bit is set to 0.

After receiving the DRV2510-Q1 address and the read-write bit, the DRV2510-Q1 device responds with an acknowledge bit. The master then sends the internal memory address byte, after which the device issues an acknowledge bit. The master device transmits another start condition followed by the DRV2510-Q1 address and the read-write bit again. On this occasion, the read-write bit is set to 1, indicating a read transfer. Next, the DRV2510-Q1 device transmits the data byte from the memory address that is read. After receiving the data byte, the master device transmits a not-acknowledge followed by a stop condition to complete the single-byte data read transfer. See the note in the Section 7.5.1 section.

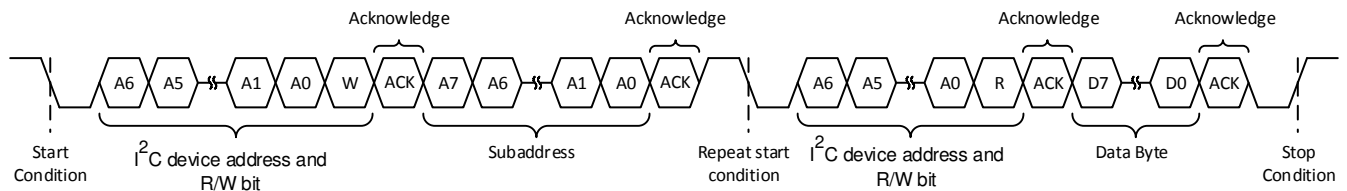


Figure 7-7. Single-Byte Read Transfer

7.5.6 Multiple-Byte Read

A multiple-byte data-read transfer is identical to a single-byte data-read transfer except that multiple data bytes are transmitted by the DRV2510-Q1 device to the master device as shown in Figure 7-8. With the exception of the last data byte, the master device responds with an acknowledge bit after receiving each data byte.

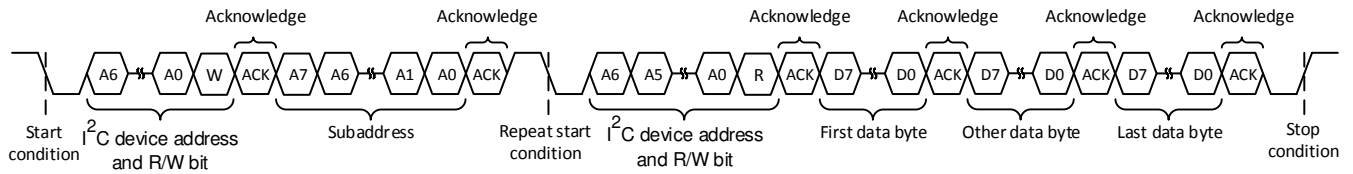


Figure 7-8. Multiple-Byte Read Transfer

7.6 Register Map

Table 7-3. Register Map Overview

| REG NO. | DEFAULT | BIT 7 | BIT 6 | BIT 5 | BIT 4 | BIT 3 | BIT 2 | BIT 1 | BIT 0 |
|---------|---------|------------|-----------|----------------------|------------|------------|-----------|----------------|----------------|
| 0x01 | 0x00 | OVER_TEMP | DC_OFFSET | OVER_VOLT | UNDER_VOLT | OVER_CURR | LOAD_DIAG | Reserved | |
| 0x02 | 0x00 | DEV_ACTIVE | STDBY | DIAG_ACTIVE | FAULT | LOAD_SHORT | LOAD_OPEN | LOAD_SHORT_GND | LOAD_SHORT_VDD |
| 0x03 | 0x00 | GAIN[1:0] | | PEAK_PROTECTION[1:2] | | | Reserved | | FREQ_SEL |

7.6.1 Address: 0x01

Figure 7-9. 0x01

| 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|--------------|--------------|--------------|---------------|--------------|--------------|----------|---|
| OVER_TEMP[0] | DC_OFFSET[0] | OVER_VOLT[0] | UNDER_VOLT[0] | OVER_CURR[0] | LOAD_DIAG[0] | Reserved | |
| RO-0 | RO-0 | RO-0 | RO-0 | RO-0 | RO-0 | | |

Table 7-4. Address: 0x01

| BIT | FIELD | TYPE | DEFAULT | DESCRIPTION | |
|-----|------------|------|---------|--|--|
| 7 | OVER_TEMP | RO | 0 | Shows the current status of the thermal protection | |
| | | | | 0 | Temperature is below the over-temperature threshold. |
| | | | | 1 | Temperature is above the over-temperature threshold. |
| 6 | DC_OFFSET | RO | 0 | Shows the status of DC offset protection | |
| | | | | 0 | DC offset protection has not occurred. |
| | | | | 1 | DC offset protection has occurred. |
| 5 | OVER_VOLT | RO | 0 | Shows the status of the over-voltage protection. | |
| | | | | 0 | VDD voltage is below the over-voltage threshold. |
| | | | | 1 | VDD voltage is above the over-voltage threshold. |
| 4 | UNDER_VOLT | RO | 0 | Shows the status of the under-voltage protection. | |
| | | | | 0 | VDD voltage is above the under-voltage threshold. |
| | | | | 1 | VDD voltage is below the under-voltage threshold. |
| 3 | OVER_CURR | RO | 0 | Shows the status of the over-current protection. | |
| | | | | 0 | An over-current event has not occurred. |
| | | | | 1 | Device shutdown due to over-current. |
| 2 | LOAD_DIAG | RO | 0 | Shows the status of the load diagnostics. | |
| | | | | 0 | An open or short has not been detected. |
| | | | | 1 | An open or short was detected. |
| 1:0 | Reserved | | | | |

7.6.2 Address: 0x02

Figure 7-10. 0x02

| 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|-------------------|--------------|--------------------|--------------|-------------------|------------------|-----------------------|-----------------------|
| DEV_ACTIVE [0] | STDBY [0] | DIAG_ACTIVE [0] | FAULT [0] | LOAD_SHORT [0] | LOAD_OPEN [0] | LOAD_SHORT_GND [0] | LOAD_SHORT_VDD [0] |
| RO-0 | RO-0 | RO-0 | RO-0 | RO-0 | RO-0 | RO-0 | RO-0 |

Table 7-5. Address: 0x02

| BIT | FIELD | TYPE | DEFAULT | DESCRIPTION | |
|-----|----------------|------|---------|--|--|
| 7 | DEV_ACTIVE | RO | 0 | Shows the device status (active or shutdown). | |
| | | | | 0 | Device is shutdown. |
| | | | | 1 | Device is active. |
| 6 | STDBY | RO | 0 | Shows the device standby status. | |
| | | | | 0 | Device is not on standby. |
| | | | | 1 | Device is on standby. |
| 5 | DIAG_ACTIVE | RO | 0 | Shows the status of the diagnostics engine. | |
| | | | | 0 | Not performing load diagnostics. |
| | | | | 1 | Performing load diagnostics. |
| 4 | FAULT | RO | 0 | Shows if a fault has occurred on the system. Either over-voltage, under-voltage, over-current, over-temperature. | |
| | | | | 0 | No fault has occurred. |
| | | | | 1 | A fault has occurred. |
| 3 | LOAD_SHORT | RO | 0 | Shows whether the output is shorted. | |
| | | | | 0 | OUT+ is not shorted to OUT-. |
| | | | | 1 | OUT+ is shorted to OUT-. |
| 2 | LOAD_OPEN | RO | 0 | Shows whether the output has a proper load connected. | |
| | | | | 0 | A proper load is connected between OUT+ and OUT-. |
| | | | | 1 | There is an open connection between OUT+ and OUT-. |
| 1 | LOAD_SHORT_GND | RO | 0 | Shows whether the output is shorted to GND. | |
| | | | | 0 | Output is not shorted to GND. |
| | | | | 1 | Either OUT+ or OUT- is shorted to GND. |
| 0 | LOAD_SHORT_VDD | RO | 0 | Shows whether the output is shorted to VDD. | |
| | | | | 0 | Output is not shorted to VDD. |
| | | | | 1 | Either OUT+ or OUT- is shorted to VDD. |

7.6.3 Address: 0x03

Figure 7-11. 0x03

| | | | | | | | |
|-----------|---|----------------------|---|---|----------|---|-------------|
| 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
| GAIN[1:0] | | PEAK_PROTECTION[2:0] | | | Reserved | | FREQ_SEL[0] |
| R/W-0 | | R/W-0 | | | R/W-0 | | R/W-0 |

Table 7-6. Address: 0x03

| BIT | FIELD | TYPE | DEFAULT | DESCRIPTION | |
|-----|----------------------|------|---------|----------------------------------|----------|
| 7:6 | GAIN[1:0] | R/W | 01 | Sets the gain. | |
| | | | | 0 | 20 dB. |
| | | | | 1 | 26 dB. |
| | | | | 2 | 32 dB. |
| | | | | 3 | 36 dB. |
| 5:3 | PEAK_PROTECTION[2:0] | R/W | 111 | Sets the peak output protection. | |
| | | | | 0 | 5V pk |
| | | | | 1 | 5.9 Vpk |
| | | | | 2 | 7 Vpk |
| | | | | 3 | 8.4 Vpk |
| | | | | 4 | 9.8 Vpk |
| | | | | 5 | 11.8 Vpk |
| | | | | 6 | 14 Vpk |
| 7 | Protection disabled | | | | |
| 2:1 | Reserved | | 00 | Always write default values | |
| 0 | FREQ_SEL | R/W | 0 | Sets the output frequency. | |
| | | | | 0 | 400 kHz. |
| | | | | 1 | 500 kHz. |

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The DRV2510-Q1 device is a high-efficiency driver for inductive loads, such as solenoids and voice-coils. The typical use of the device is on haptic applications where short, strong waveforms are desired to create a haptic event that will be coming from the application processor.

8.2 Typical Applications

8.2.1 Single-Ended Source

To use the DRV2510-Q1 with a single-ended source, apply either a voltage divider to bias IN- to 3 V, or use a 0.1- μ F cap from IN- to GND to have the device self bias. Apply the single-ended signal to the IN+ pin through an AC coupling capacitor.

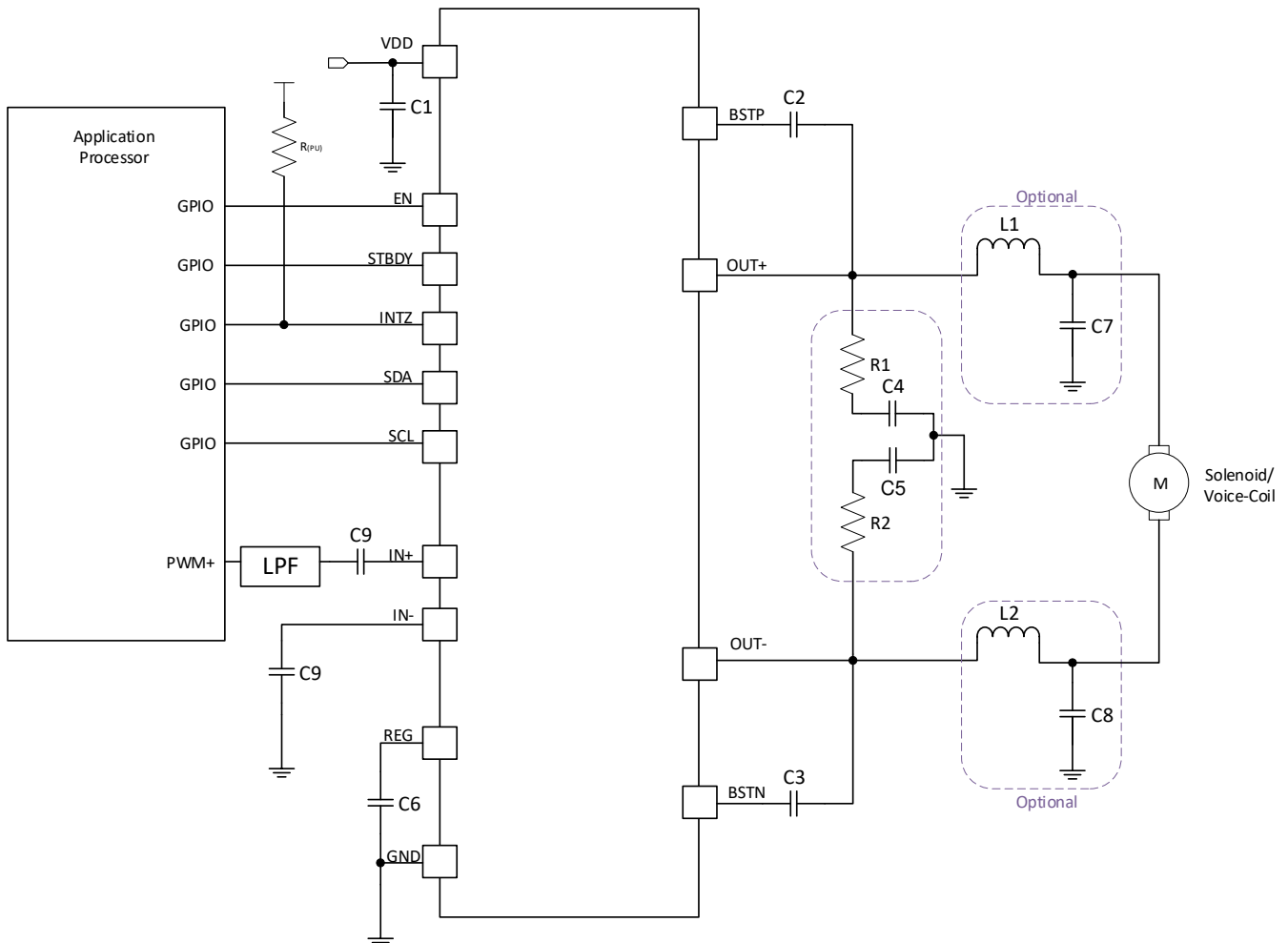


Figure 8-1. Typical Application Schematic

8.2.1.1 Design Requirements

For most applications the following component values found in [Table 8-1](#) below can be used.

Table 8-1. Component Requirements Table

| COMPONENT | DESCRIPTION | SPECIFICATION | TYPICAL VALUE |
|-------------------|----------------------------|---------------|---|
| C1 | Supply capacitor | Capacitance | 22 μ F, 10 μ F, and 0.1 μ F |
| C2/C3 | Boost capacitor | Capacitance | 0.22 μ F |
| C4/C5 | Output snubber capacitor | Capacitance | 470 pF |
| C6 | Regulator capacitor | Capacitance | 1 μ F |
| C9 | Input decoupling capacitor | Capacitance | 0.1 μ F |
| R1/R2 | Output snubber resistor | Resistance | 3.3 Ω |
| R _(PU) | Pull-up resistor | Resistance | 100 k Ω |

8.2.1.2 Detailed Design Procedure

8.2.1.2.1 Optional Components

Note that in the diagrams, there are a few optional external components. These optional external components may be needed in the application to meet EMI/EMC standards and specifications by filters necessary frequency spectrums.

8.2.1.2.2 Capacitor Selection

A bulk bypass capacitor should be mounted between VBAT and GND. The capacitance needs to be >22 μ F with a X5R or better rating on the power pins to GND. Also include two ceramic capacitors in the ranges of 220 pF to 1 μ F and 100 nF to 1 μ F. The bootstrap capacitors, BSTP and BSTN, should be 220-nF ceramic capacitors of quality X5R or better rated for at least the maximum rating of the pin.

8.2.1.2.3 Solenoid Selection

The DRV2510-Q1 solenoid driver can accommodate a variety of solenoids. Solenoids should have an equivalent resistance of 1.6 Ω or greater. Solenoids with lower resistances are prone to driving high currents. A maximum peak current of 3-A should not be exceeded.

8.2.1.2.4 Output Filter Considerations

The output filter is optional and is mainly for limiting peak currents. A second-order Butterworth low-pass filter with the cut-off frequency set to a few kilohertz should be sufficient. See [Equation 1](#), through [Equation 4](#), for example filter design.

$$H(s) = \frac{1}{s^2 + \sqrt{2}s + 1} \quad (1)$$

$$L_x = \frac{\sqrt{2} \times R_L}{2\omega_0} \quad (2)$$

$$2 \times C_F = \frac{\sqrt{2}}{2 \times \frac{R_L}{2} \times \omega_0} \quad (3)$$

$$\omega_0 = 2\pi \times f \quad (4)$$

8.2.1.3 Application Curves

These application curves were taken using an HA200 solenoid with a 100-g mass, and the acceleration was measured using the DRV-AAC16-EVM accelerometer. The following scales apply to the graphs:

- Output Differential Voltage scale is shown on the plots at 5-V/div
- Acceleration scale is 5.85-G/div
- Current scale is 2-A/div

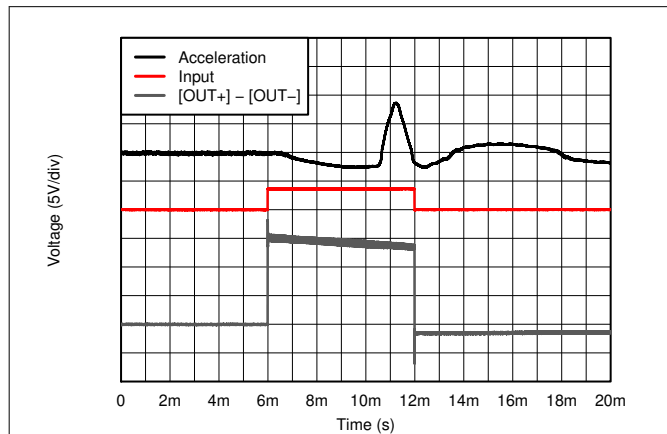


Figure 8-2. Voltage and Acceleration vs Time (Input Square Wave)

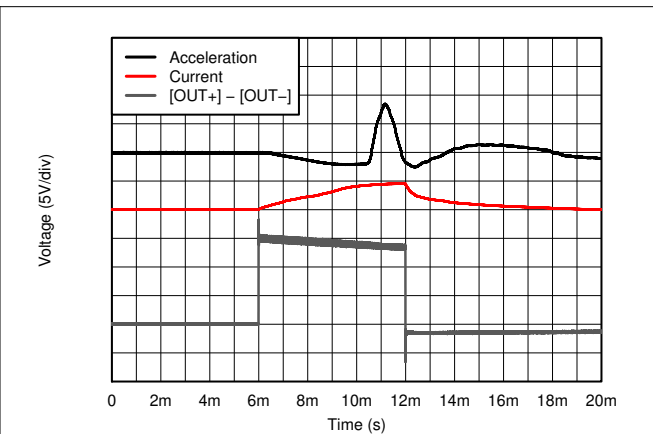


Figure 8-3. Voltage and Acceleration vs Time (Square Wave)

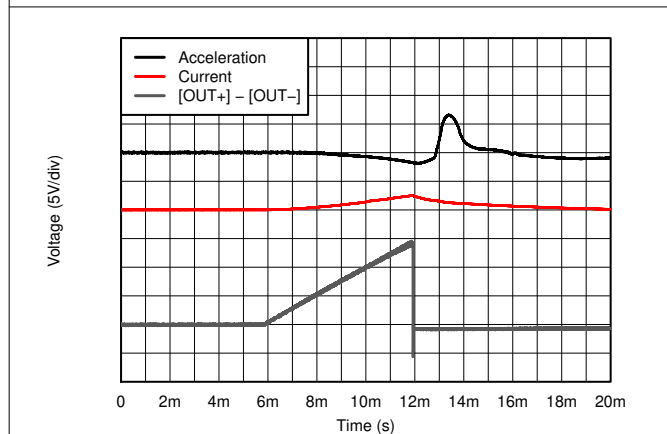


Figure 8-4. Voltage and Acceleration vs Time (Ramp Wave)

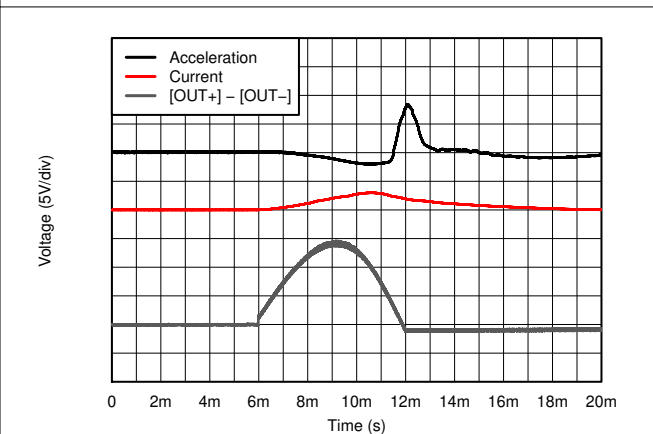


Figure 8-5. Voltage and Acceleration vs Time (1/2 Sine Wave)

8.2.1.4 Differential Input Diagram

To use the DRV2510-Q1 with a differential input source, apply both inputs differentially through AC coupling capacitors from a control source (GPIO, DAC, etc...).

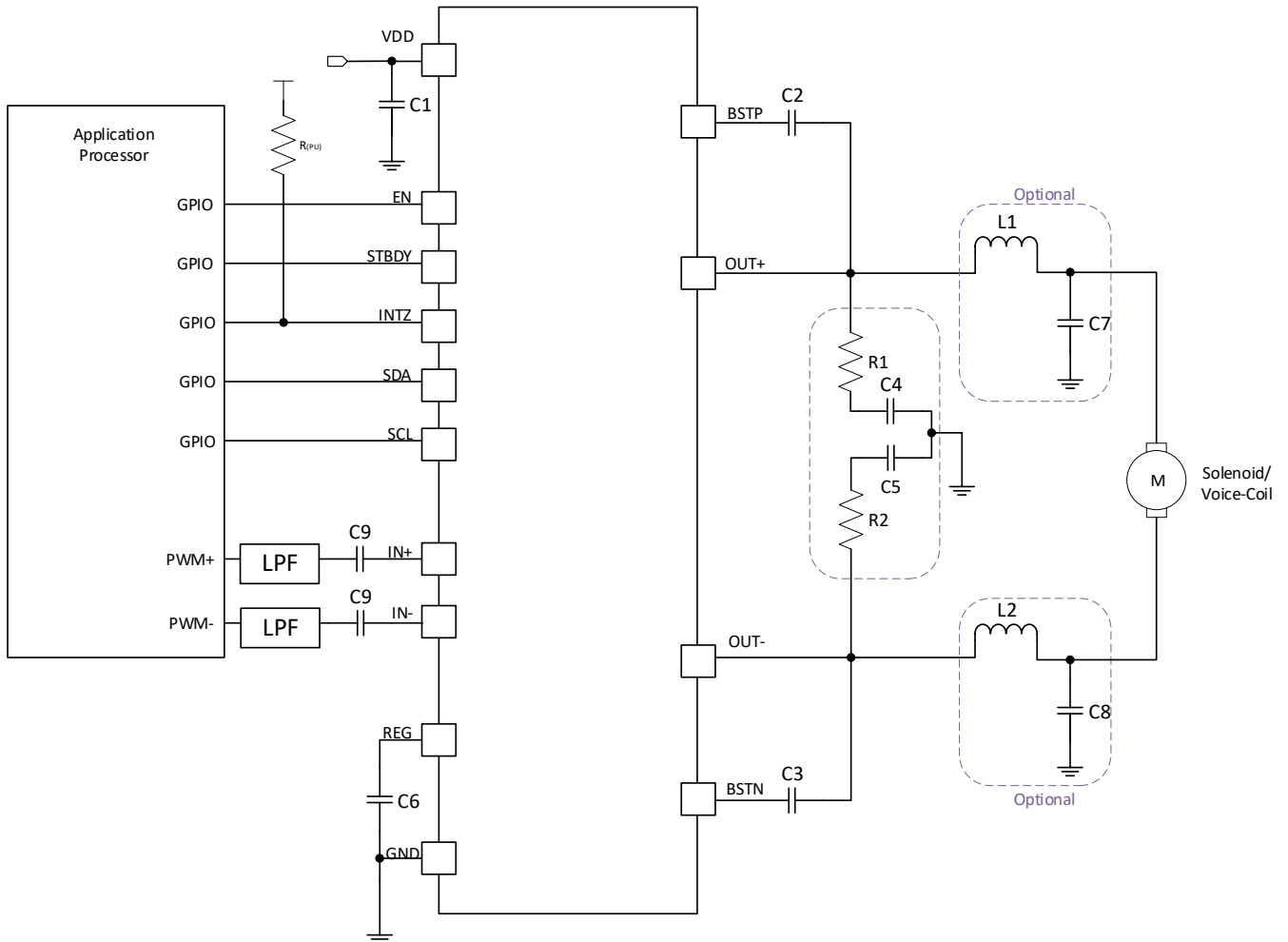


Figure 8-6. Typical Application Schematic

9 Power Supply Recommendations

The DRV2510-Q1 device operates from 4.5 V - 18 V and this supply should be able to handle high surge currents in order to meet the high current draws for haptics effects. Additionally the DRV2510-Q1 should have 22- μ F, 10- μ F and 0.1- μ F ceramic capacitors near the VDD pin for additional decoupling from trace routing.

10 Layout

10.1 Layout Guidelines

The EVM layout optimizes for thermal dissipation and EMC performance. The DRV2510-Q1 device has a thermal pad down, and good thermal conduction and dissipation require adequate copper area. Layout also affects EMC performance. It is best practice to use the same/similar layout as shown below in the DRV2510Q1EVM.

10.2 Layout Example

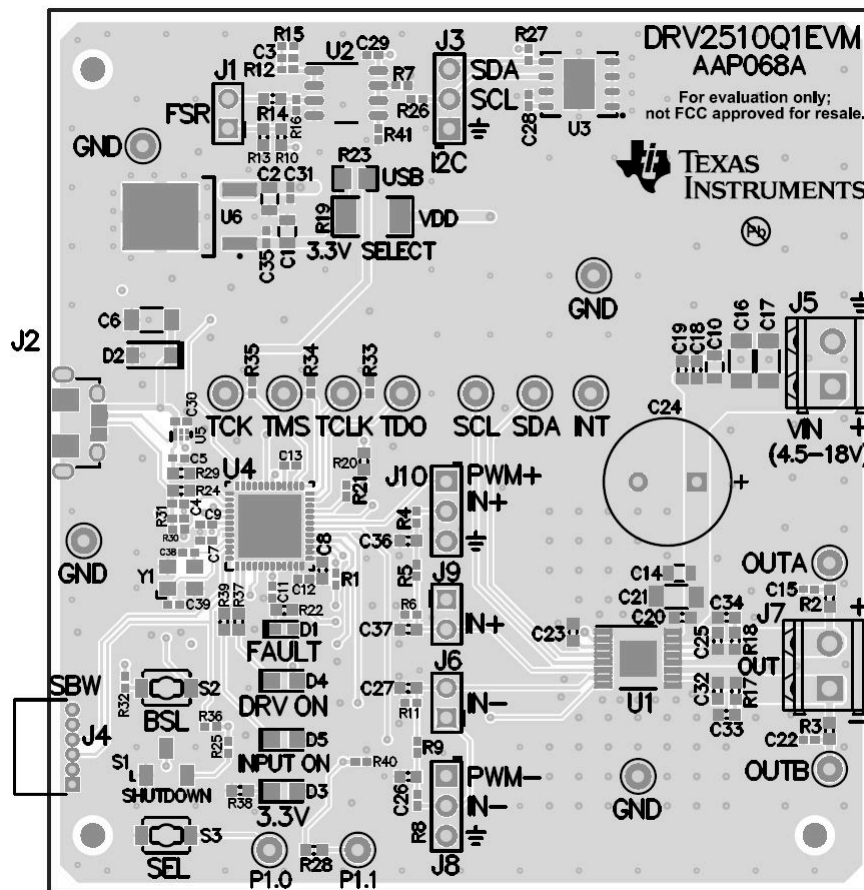


Figure 10-1. DRV2510-Q1 EVM

11 Device and Documentation Support

11.1 Device Support

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11.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

| Orderable Device | Status (1) | Package Type | Package Drawing | Pins | Package Qty | Eco Plan (2) | Lead finish/ Ball material (6) | MSL Peak Temp (3) | Op Temp (°C) | Device Marking (4/5) | Samples |
|------------------|---------------|--------------|-----------------|------|-------------|-----------------|--------------------------------------|----------------------|--------------|-------------------------|---------|
| DRV2510QPWPRQ1 | ACTIVE | HTSSOP | PWP | 16 | 2000 | RoHS & Green | NIPDAU | Level-3-260C-168 HR | -40 to 125 | DRV2510 | Samples |

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

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(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

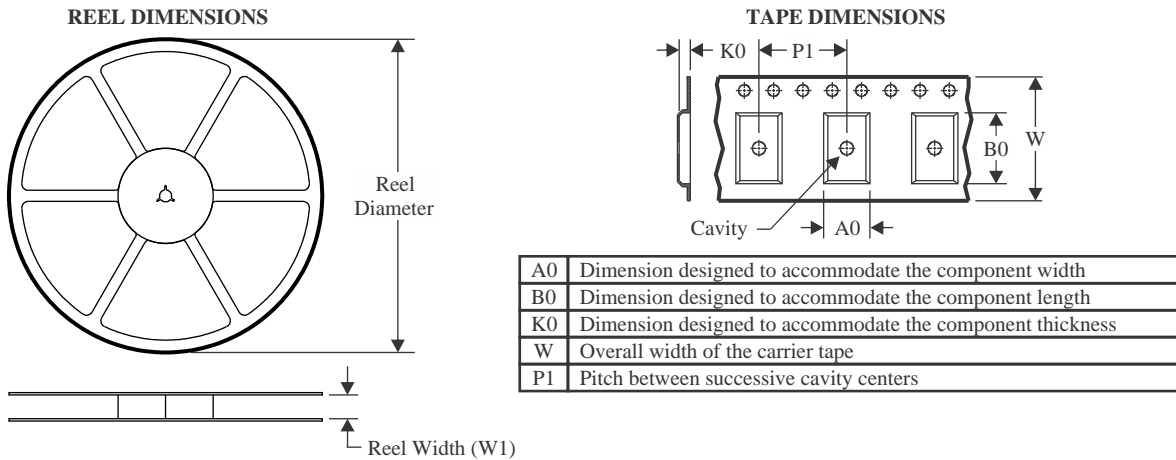
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

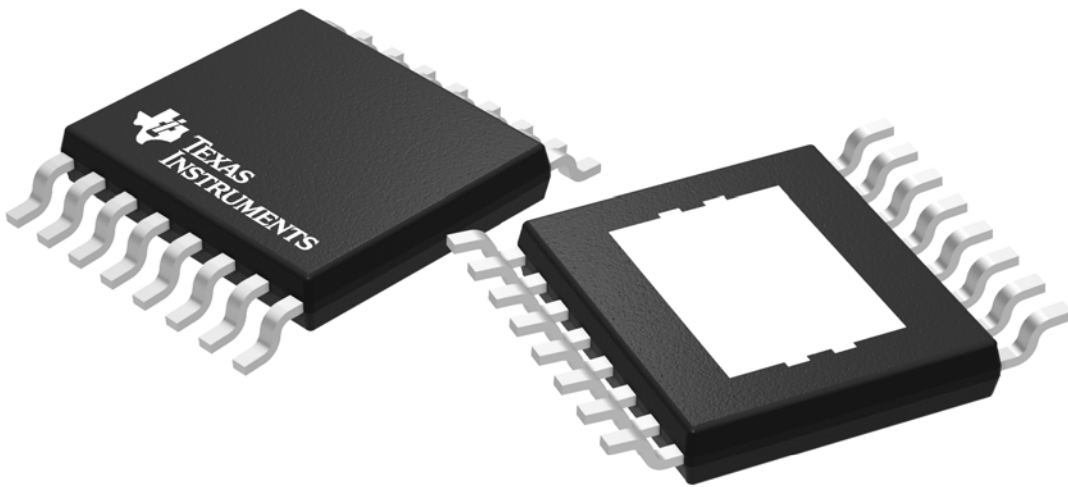

*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|---------------|--------------|-----------------|------|------|--------------------|--------------------|---------|---------|---------|---------|--------|---------------|
| DRV2510QPWRQ1 | HTSSOP | PWP | 16 | 2000 | 330.0 | 12.4 | 6.9 | 5.6 | 1.6 | 8.0 | 12.0 | Q1 |

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
|----------------|--------------|-----------------|------|------|-------------|------------|-------------|
| DRV2510QPWPRQ1 | HTSSOP | PWP | 16 | 2000 | 350.0 | 350.0 | 43.0 |



Images above are just a representation of the package family, actual package may vary.
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